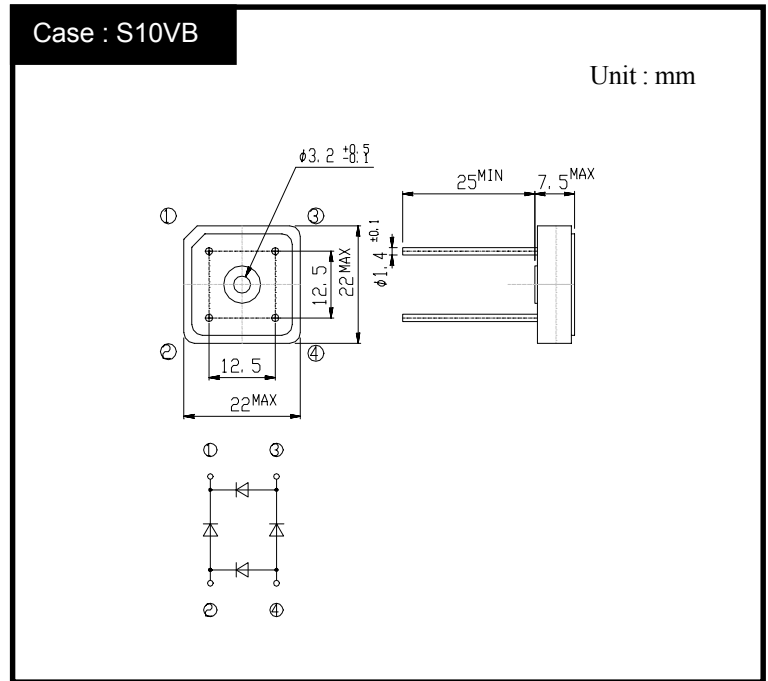


S10VB20

200V 10A

OUTLINE DIMENSIONS



RATINGS

● Absolute Maximum Ratings

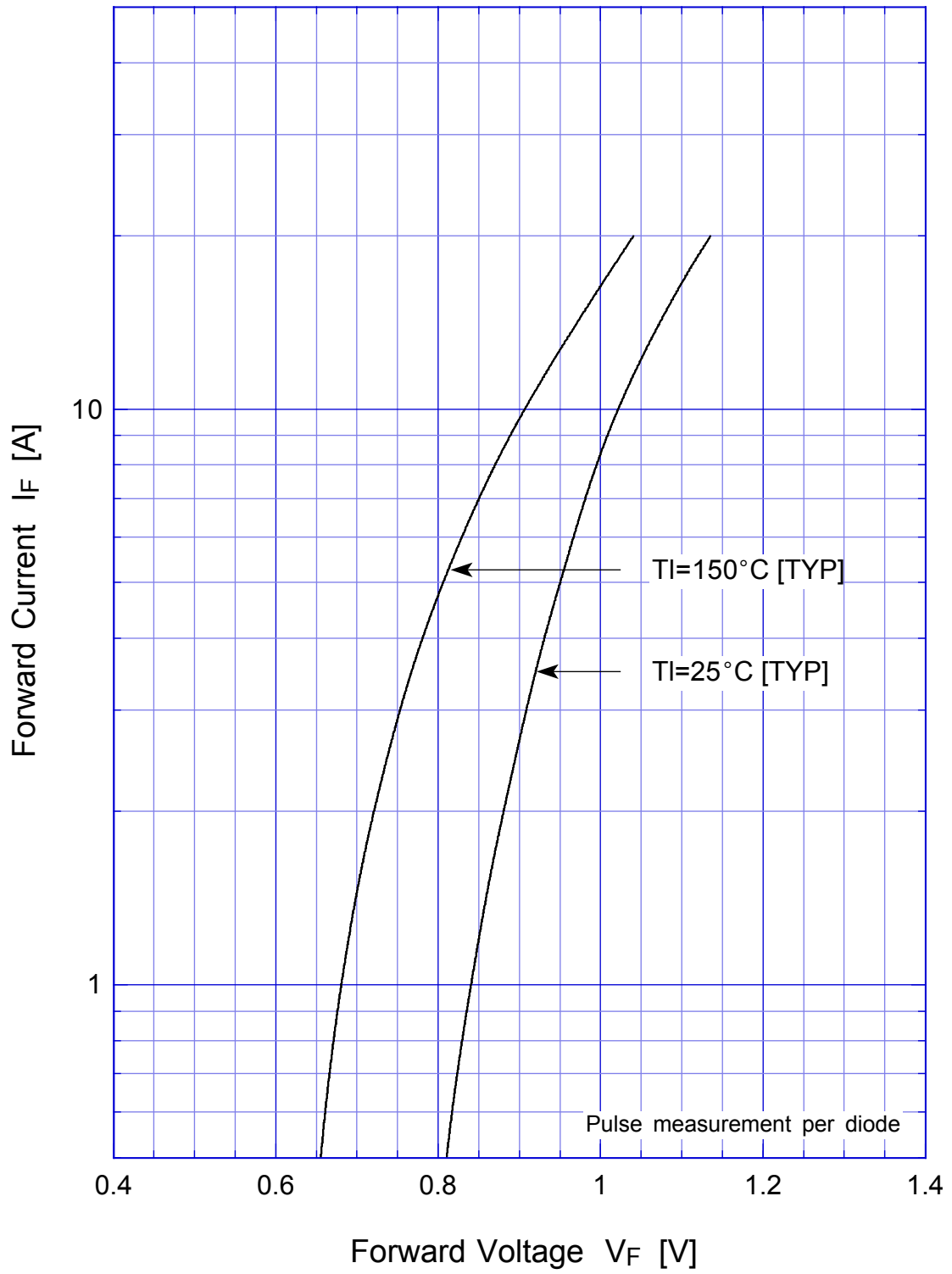
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-40~150	°C
Operating Junction Temperature	T _j		150	°C
Maximum Reverse Voltage	V _{RM}		200	V
Average Rectified Forward Current	I _O	50Hz sine wave, R-load, T _a =40°C With heatsink, θ _{fa} =2.4°C/W	10	A
		50Hz sine wave, R-load, T _a =40°C Without heatsink	3.7	
Peak Surge Forward Current	I _{FSM}	50Hz sine wave, Non-repetitive 1cycle peak value, T _j =25°C	200	A
Current Squared Time	I ² t	1ms ≤ t < 10ms T _c =25°C	110	A ² s
Dielectric Strength	V _{dis}	Terminals to case, AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque : 0.5N·m)	0.8	N·m

● Electrical Characteristics (Tl=25°C)

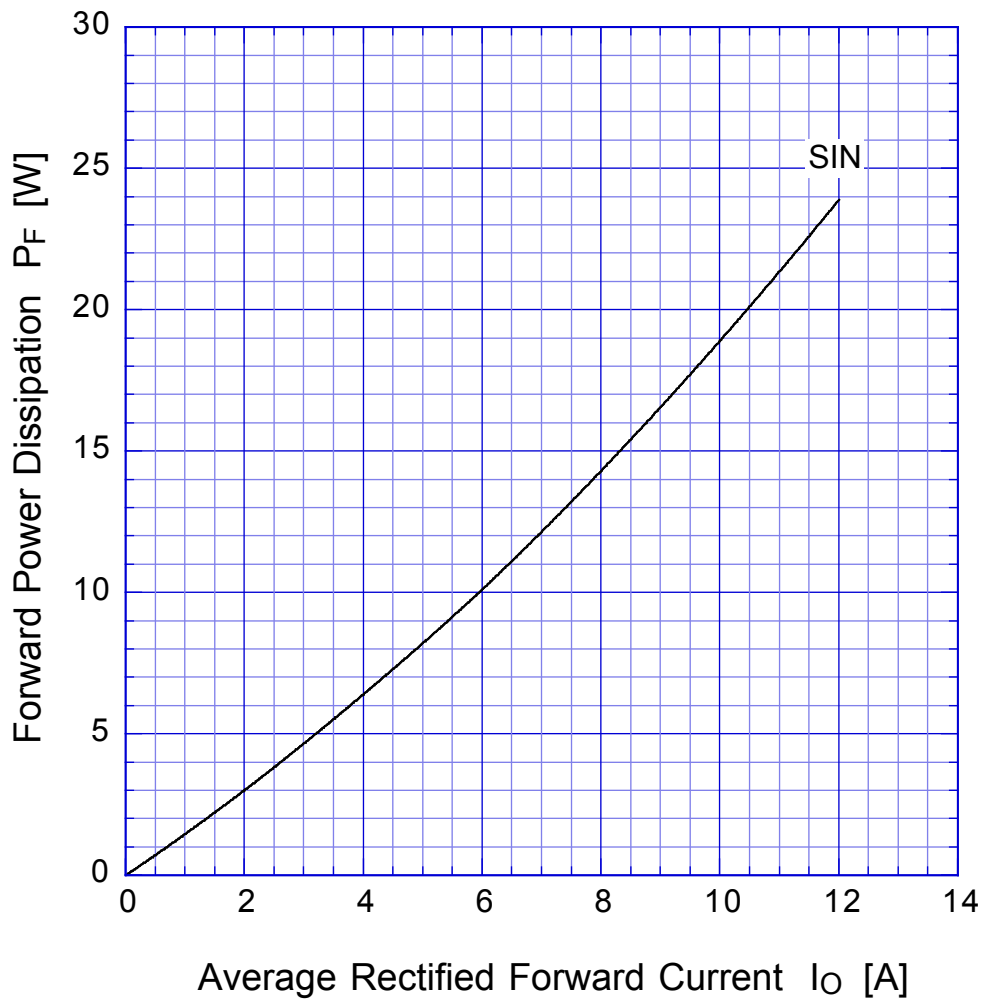
Item	Symbol	Conditions	Ratings	Unit
Forward Voltage	V _F	I _F =5A, Pulse measurement, Rating of per diode	Max.1.05	V
Reverse Current	I _R	V _R =V _{RM} , Pulse measurement, Rating of per diode	Max.10	μA
Thermal Resistance	θ _{jl}	junction to lead	Max.2.8	°C/W

S10VBx

Forward Voltage



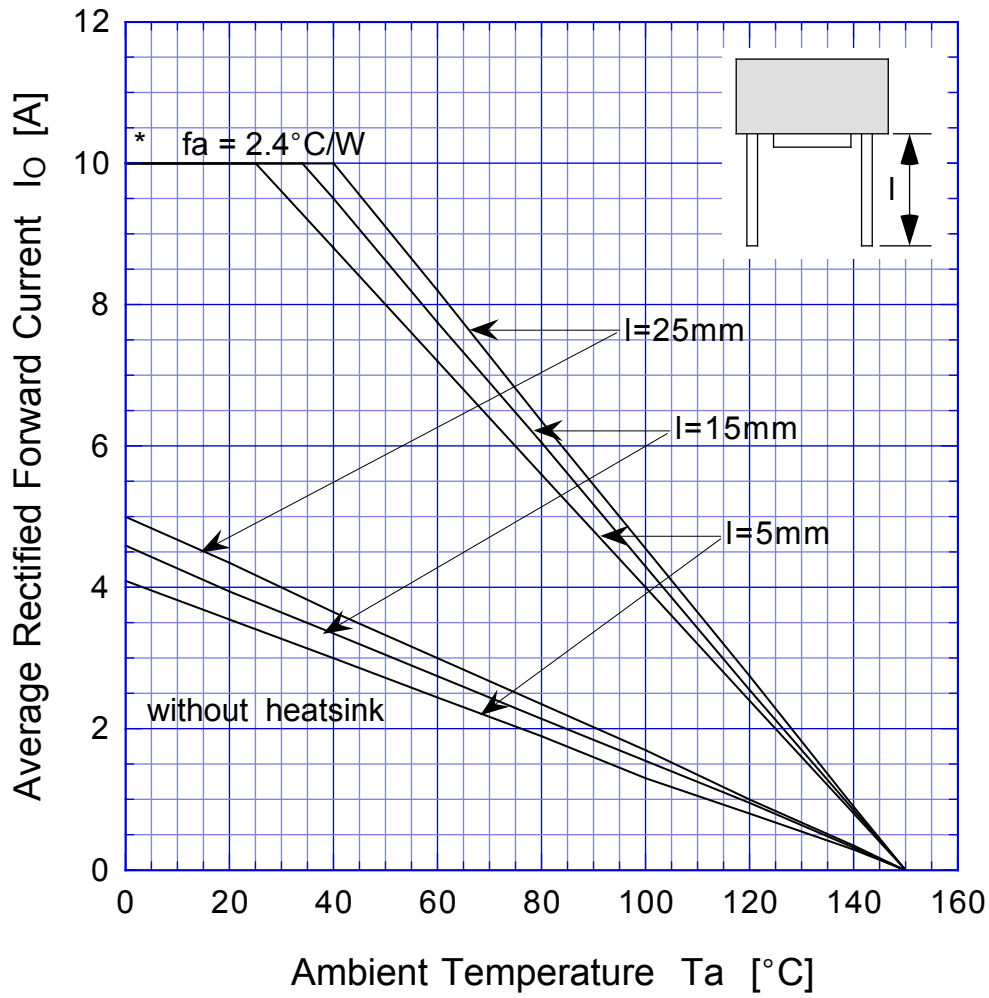
S10VBx Forward Power Dissipation



$T_j = 150^\circ\text{C}$
Sine wave

S10VBx

Derating Curve



Sine wave

R-load

Free in air

* with thermal compound, TOR=5kg-cm

S10VBx

Peak Surge Forward Capability

